WEST Search History

DATE: Wednesday, June 25, 2003

Set Name side by side	Query	Hit Count	Set Name result set
DB=USPT,PGPB,JPAB,EPAB,DWPI,TDBD; PLUR=YES; OP=OR			
L15	l4 and l11	63	L15
L14	l12 and l13	202	L14
L13	source and drain	247069	L13
L12	l10 and l11	202	L12
L11	ldd or (light$4 adj dop$4)	25721	L11
L10	l7 and l9	230	L10
L9	l8 adj4 drain	457	L9
L8	double adj diffus$4	3977	L8
L7	spacer$	312447	L7
L6	sapcer$	62	L6
L5	l1 and l4	1	L5
L4	l3 adj3 drain	81	L4
L3	double adj dop$4	262	L3
L2	5716861	53	L2
L1	5716861	53	L1

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L2: Entry 1 of 1 File: DWPI Oct 22, 2002

DERWENT-ACC-NO: 1998-569916
DERWENT-WEEK: 200273

TITLE: Open structure, especially photonic crystal production - by etching selectively doped layers of material having doping-dependent etchability

INVENTOR: GRUENING, U; LEHMANN, V ; REISINGER, H ; STENGL, R ; WENDT, H

PATENT-ASSIGNEE: SIEMENS AG (SIEI), INFINEON TECHNOLOGIES AG (INFN)

PRIORITY-DATA: 1997DE-1043296 (September 30, 1997)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
US 6468348 B1	October 22, 2002		000	C30B025/04
DE 19743296 C1	November 12, 1998		006	B32B001/10
WO 9917349 A1	April 8, 1999	G	000	H01L021/306
KR 2001030753 A	April 16, 2001		000	H01S003/08
JP 2001518707 W	October 16, 2001		018	H01L021/306

DESIGNATED-STATES: JP KR US AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE

APPLICATION-DATA:

PUB-NO	APPL-DATE	APPL-NO	DESCRIPTOR
US 6468348B1	August 21, 1998	1998WO-DE02450	Cont of
US 6468348B1	March 30, 2000	2000US-0539237	
DE 19743296C1	September 30, 1997	1997DE-1043296	
WO 9917349A1	August 21, 1998	1998WO-DE02450	
KR2001030753A	March 28, 2000	2000KR-0703309	
JP2001518707W	August 21, 1998	1998WO-DE02450	
JP2001518707W	August 21, 1998	2000JP-0514317	
JP2001518707W		WO 9917349	Based on

INT-CL (IPC): B32 B 1/10; B32 B 31/10; C23 F 1/02; C30 B 25/02; C30 B 25/04; C30 B 31/06; C30 B 33/10; G02 B 1/02; G02 B 6/12; H01 L 21/306; H01 S 3/08

ABSTRACTED-PUB-NO: DE 19743296C
BASIC-ABSTRACT:

Production of an open structure (3), consisting of two-dimensionally structured layers of material with doping-dependent etchability, involves: (a) preparing a first layer and doping one or more zones to mark a structure portion; (b) applying one or more further layers and doping one or more zones of the layer(s) to mark a structure portion; and (c) etching away each non-marked portion. Preferably, the material is a semiconductor (especially silicon) in single crystal form for the first layer and in epitaxially grown form for the further layer(s) and selective

p-doping is carried out with boron using masks.

USE - Used for producing a photonic crystal useful for confining optical waveguides or optical cavity resonators.

ADVANTAGE - The process produces an open monolith with a no more than fourfold periodically repetitive structure by means of semiconductor device technology thus allowing integration of photonic crystal technology with semiconductor optoelectronics technology.

ABSTRACTED-PUB-NO: DE 19743296C
EQUIVALENT-ABSTRACTS:

CHOSEN-DRAWING: Dwg.1/5

DERWENT-CLASS: L03 P73 P81 U11 V07 V08
CPI-CODES: L03-G02; L04-A01;
EPI-CODES: U11-C18B9; V07-F01A5; V08-A01A;